

## **isc Silicon PNP Power Transistor**

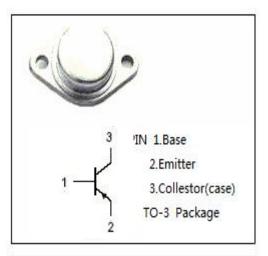
# BD312

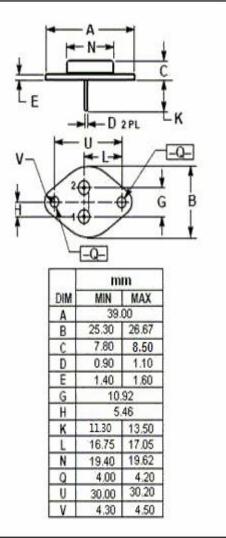
#### DESCRIPTION

- Excellent Safe Operating Area
- DC Current Gain-h<sub>FE</sub>= 25(Min.)@I<sub>C</sub> = -5A
- Collector-Emitter Saturation Voltage-: V<sub>CE(sat</sub>)= -1.0 V(Max)@ I<sub>C</sub> = -5A
- Complement to Type BD311
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

• Designed for high quality amplifiers operating up to 60 watts into 4 ohm load.





### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	-60	V
VCEO	Collector-Emitter Voltage	-60	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
lc	Collector Current-Continuous	-10	A
I <sub>CM</sub>	Collector Current-Peak	-20	A
I <sub>B</sub>	Base Current-Continuous	-4	A
Pc	Collector Power Dissipation@T <sub>c</sub> =25℃	115	W
TJ	Junction Temperature	200	°C
T <sub>stg</sub>	Storage Temperature	-65~200	°C

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT	
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.52	°C/W	

1



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### ELECTRICAL CHARACTERISTICS

### $T_{c}\text{=}25^{\circ}\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = -30mA; I <sub>B</sub> =0	-60		V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -5A; I <sub>B</sub> = -0.5A		-1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -5A; I <sub>B</sub> = -0.5A		-1.8	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -5A; V <sub>CE</sub> = -4V		-1.5	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = -60V; I <sub>B</sub> = 0		-1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -7.0V; I <sub>C</sub> = 0		-1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -5A; V <sub>CE</sub> = -4V	25		
h <sub>FE-2</sub>	DC Current Gain	Ic= -10A; Vce= -4V	5		
I <sub>s/b</sub>	Second Breakdown Collector Current with Base Forward Biased	V <sub>CE</sub> = -39V,t= 0.5s V <sub>CE</sub> = -50V,t= 0.5s	-2.95 -0.60		A
f⊤	Current Gain-Bandwidth Product	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -10V;f=1.0MHz	4		MHz

### **NOTICE:**

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